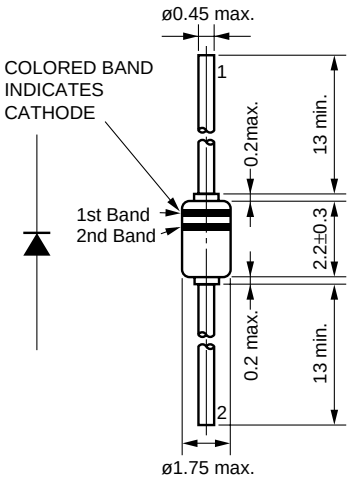
MA719

Silicon epitaxial planer type

For high-frequency rectification

Unit : mm



1 : Cathode
2 : Anode
JEDEC : DO-34

■ Features

- DO-34 (DHD) package, enabling rectification at $I_{F(AV)}$= 500mA
- High-density mounting (5mm pitch insertion) possible
- Fast t_{rr} (reverse recovery time), optimum for high-frequency rectification
- Low V_F (forward rise voltage), with high rectification efficiency
- Glass sealed package with high reliability

■ Absolute Maximum Ratings (Ta= 25˚C)

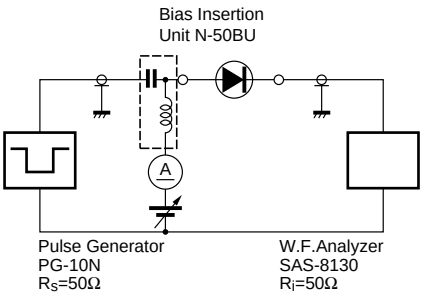
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Repetitive peak reverse voltage	V_{RRM}	40	V
Peak forward current	I_{FM}	1	A
Average forward current	$I_{F(AV)}$	500	mA
Non-repetitive peak forward surge current	I_{FSM}*	3	A
Junction temperature	T_j	125	˚C
Storage temperature	T_{stg}	– 55 to + 125	˚C

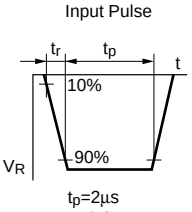
* 50Hz sine wave, one-cycle wave, high value (non-repetitive)

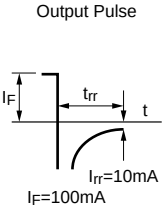
■ Electrical Characteristics (Ta= 25˚C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R = 35V			100	µA
Forward voltage (DC)	V_F	I_F = 500mA			0.55	V
Terminal capacitance	C_t	V_R = 0V, f=1MHz		60		pF
Reverse recovery time	t_{rr}*	$I_F = I_R$=100mA I_{rr}=10mA, R_L=100Ω		5		ns

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 400MHz
3. * t_{rr} measuring circuit



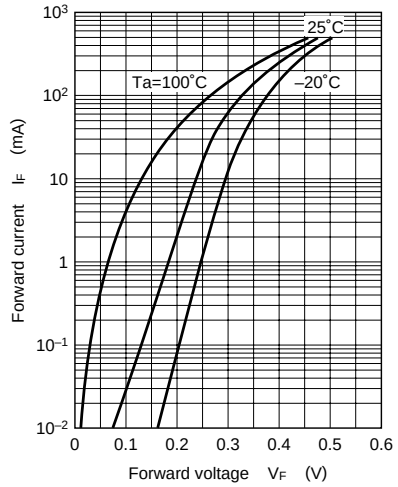




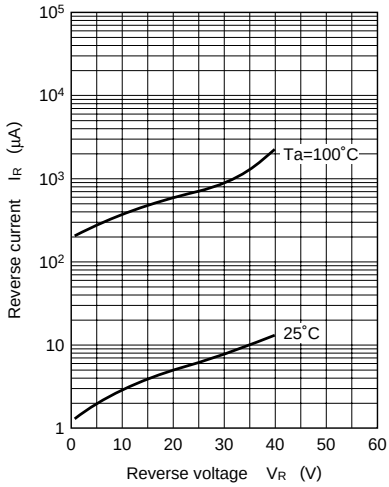
■ Cathode Indication

	1st Band	2nd Band
Color	Silver	Silver

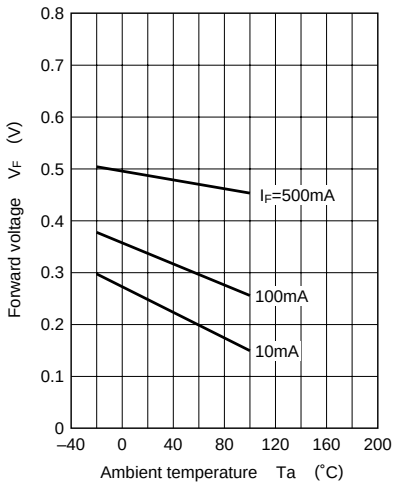
$I_F - V_F$



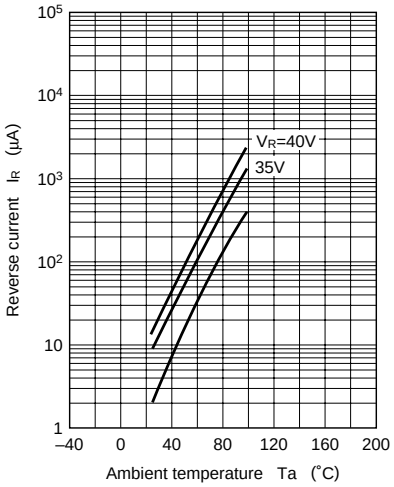
$I_R - V_R$



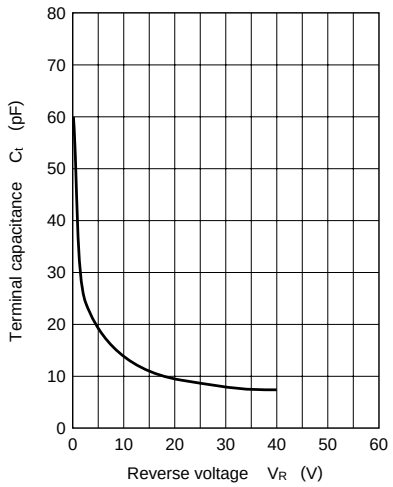
$V_F - Ta$



$I_R - Ta$



$C_t - V_R$



$I_{F(surge)} - t_W$